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(54) **EPI FACET HEIGHT UNIFORMITY  
IMPROVEMENT FOR FDSOI  
TECHNOLOGIES**

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(71) Applicant: **GLOBALFOUNDRIES Inc.**, Grand  
Cayman (KY)

(57) **ABSTRACT**

(72) Inventors: **George Robert MULFINGER**, Wilton,  
NY (US); **Xusheng WU**, Ballston Lake,  
NY (US)

A method of controlling the facet height of raised source/  
drain epi structures using multiple spacers, and the resulting  
device are provided. Embodiments include providing a gate  
structure on a SOI layer; forming a first pair of spacers on  
the SOI layer adjacent to and on opposite sides of the gate  
structure; forming a second pair of spacers on an upper  
surface of the first pair of spacers adjacent to and on the  
opposite sides of the gate structure; and forming a pair of  
faceted raised source/drain structures on the SOI, each of the  
faceted source/drain structures faceted at the upper surface  
of the first pair of spacers, wherein the second pair of spacers  
is more selective to epitaxial growth than the first pair of  
spacers.

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